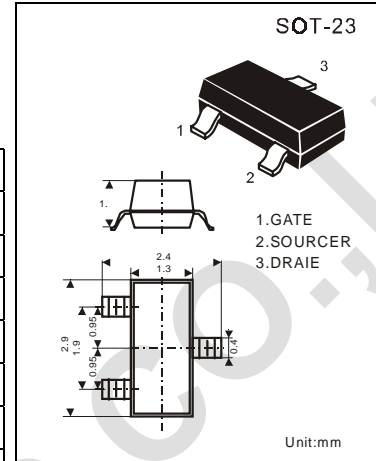


FEATURES

- * Low current(100mA)
- * Low voltage(32V)
- * General purpose switching and amplification

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	32	V
Collector-Emitter Voltage	Vceo	32	V
Emitter-Base Voltage	Veb	5	V
Collector Current	Ic	100	mA
Collector Dissipation Ta=25°C*	P _D	250	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65-150	°C



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	32			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	32			V	Ic= 2mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	5			V	Ie= 100uA Ic=0
Collector Cutoff Current	Icbo			100 10	nA uA	Vcb= 32V Ie=0 Vcb=32V Ie=0 Tj=100°C
Emitter Cutoff Current	Iebo			100	nA	Veb=5V Ic=0
Base-Emitter Voltage	Vbe	550		700	mV	Ic=2mA Vce=5V
Collector Capacitance	Cob		2.5		pF	Ie=0 Vcb=10V f=1MHz
DC Current Gain	Hfe		190			Vce= 5V Ic= 10uA
			110	220		Vce= 5V Ic= 2mA
Collector-Emitter Saturation Voltage	Vce(sat)		120 210	250	mV	Ic= 10mA Ib= 0.5mA Ic=50mA Ib=2.5mA
Base-Emitter Saturation Voltage	Vbe(sat)		750 850		mV	Ic= 10mA Ib= 0.5mA Ic=50mA Ib=2.5mA
Transition Frequency	f _T	100			MHz	Vce=5V Ic=10mA f=100MHz
Noise figure	F			10	dB	Ic=200uA Vce=5V Rs=2k F=1kHz B=200Hz

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25°C.

Pulse Test : Pulse Width≤300uS,Duty cycle≤2%

DEVICE MARKING:

BCW31=D1t